



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

Feature

- $BV_{CEV} > 500V$
- $BV_{ECV} > 6V$ reverse blocking
- $I_C = 150mA$ high Continuous Collector Current
- I_{CM} Up to 500mA Peak Pulse Current
- 625mW Power Dissipation
- Low Saturation Voltage $< -90mV @ 50mA$
- Excellent h_{FE} Characteristics Up To 120mA

Mechanical Data

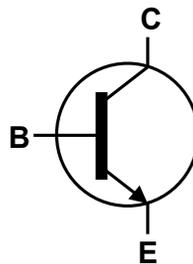
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per
MIL-STD-202, Method 208 ^(e3)
- Weight 0.008 grams (approximate)

Applications

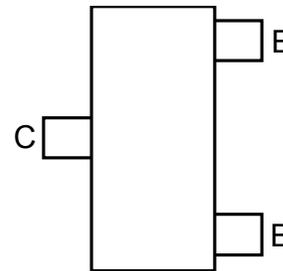
- Automotive
- Off-line switching applications
- RCD circuits
- PFC disable switch in PSU
- Emergency lighting
- Piezo actuators
- Telecom protected line switching



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	500	V
Collector-Emitter Voltage	V _{CEV}	500	V
Collector-Emitter Voltage	V _{CEO}	450	V
Emitter-Base Voltage	V _{EBO}	7	V
Emitter-Collector Voltage	V _{ECV}	6	V
Continuous Collector Current	I _C	150	mA
Peak Pulse Current	I _{CM}	500	mA
Base Current	I _B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

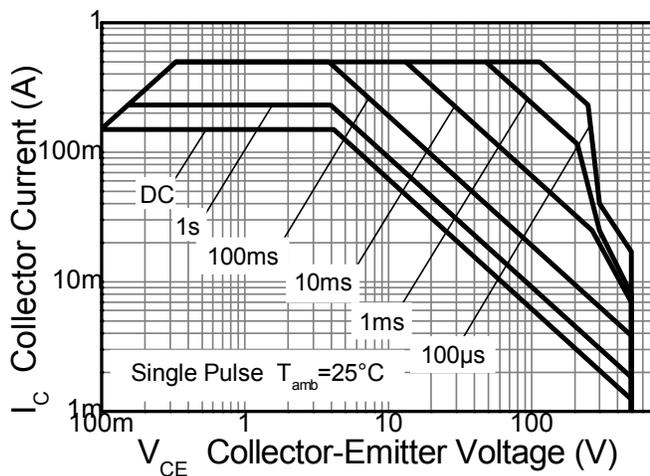
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	625	mW
Power Dissipation (Note 7)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{θJL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

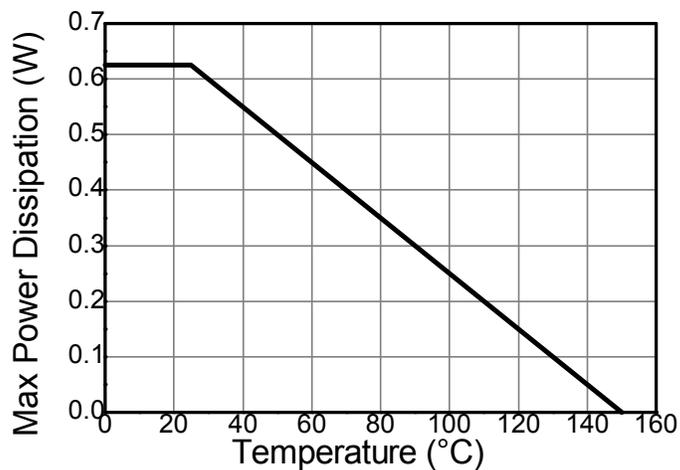
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as note 6, except the device is measured at t ≤ 5 sec.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

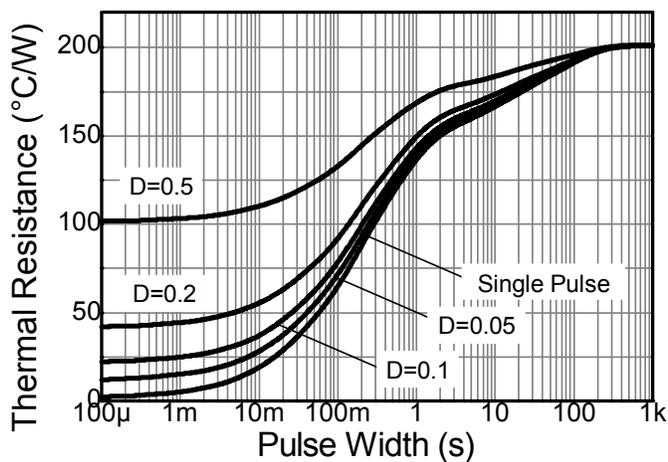
Thermal Characteristics and Derating Information



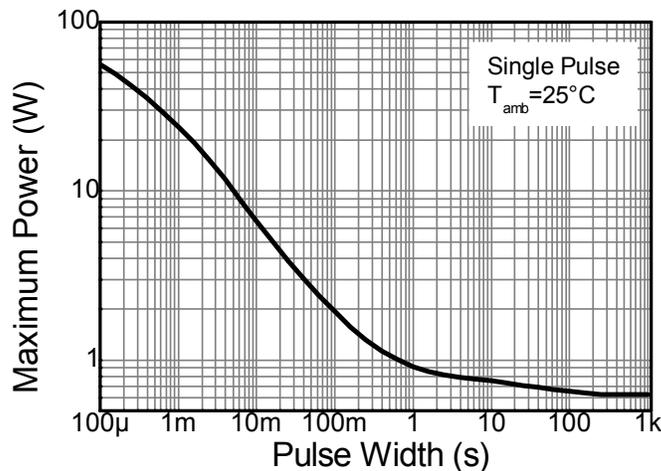
Safe Operating Area



Derating Curve



Transient Thermal Impedance



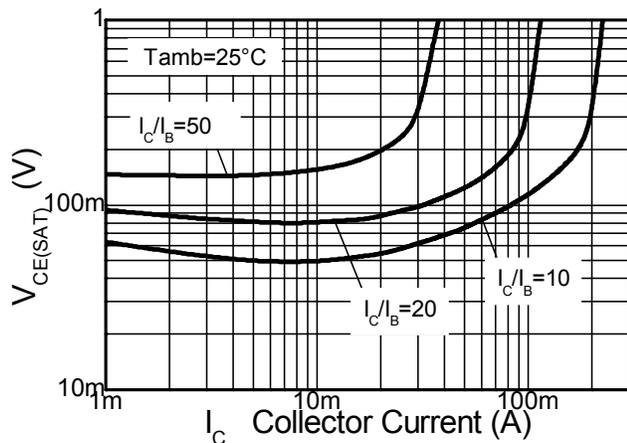
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

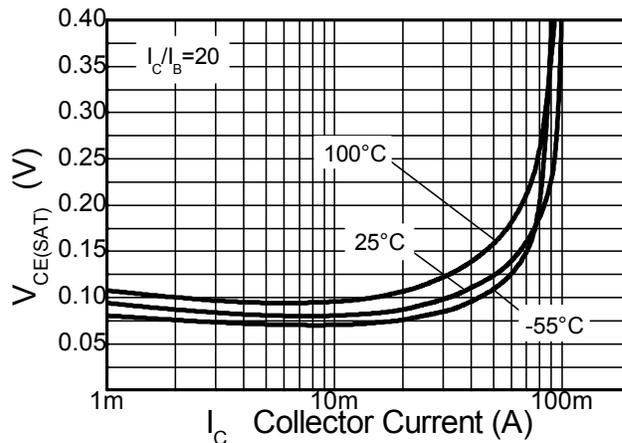
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	500	700	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	500	700	—	V	I _C = 10μA; 0.3V > V _{BE} > -1V
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	450	500	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	—	V	I _E = 100μA
Emitter-Base Breakdown Voltage (Reverse Blocking)	BV _{ECV}	6	8.1	—	V	I _C = 1μA; 0.3V > V _{BC} > -6V
Collector Cutoff Current	I _{CBO}	—	<10	100	nA	V _{CB} = 450V
Emitter Cutoff Current	I _{EBO}	—	<10	100	nA	V _{EB} = 5.6V
Collector Emitter Cutoff Current	I _{CES}	—	<10	100	nA	V _{CE} = 450V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	50 —	120 70	— —	—	I _C = 30mA, V _{CE} = 10V I _C = 50mA, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	— —	60 70	75 90	mV mV	I _C = 20mA, I _B = 2mA I _C = 50mA, I _B = 6mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	—	0.71	0.9	V	I _C = 50mA, V _{CE} = 10V
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	—	0.76	0.9	V	I _C = 50mA, I _B = 5mA
Output Capacitance	C _{obo}	—	—	5	pF	V _{CB} = 20V, f = 1MHz
Transition Frequency	f _T	50	—	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 20MHz
Turn-On Time	t _{on}	—	113	—	ns	V _C = 100V, I _C = 50mA
Turn-Off Time	t _{off}	—	3450	—	ns	I _{B1} = 5mA, I _{B2} = -10mA

Notes: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

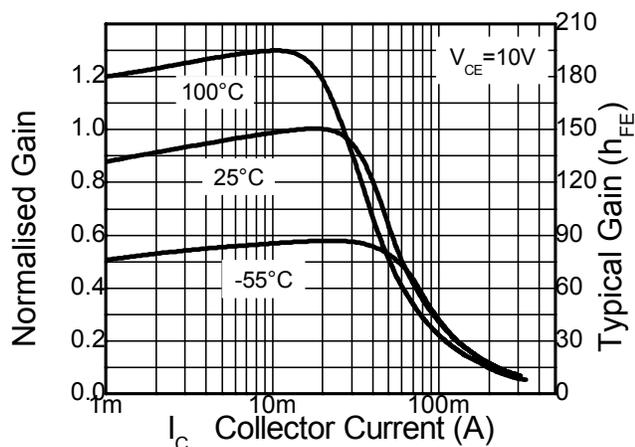
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



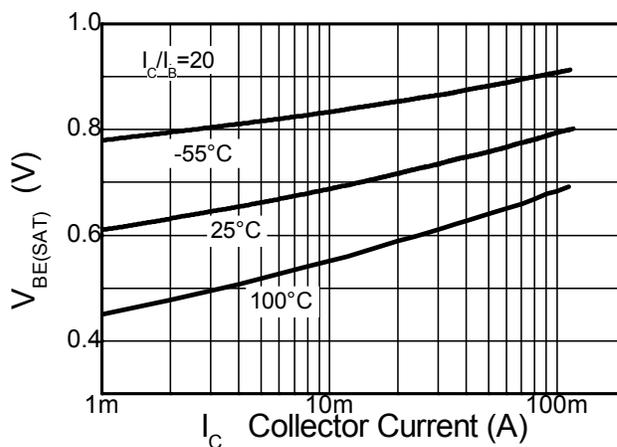
$V_{CE(SAT)} \ v \ I_C$



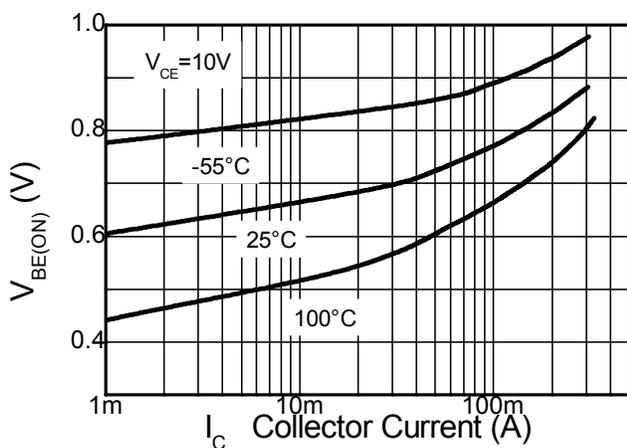
$V_{CE(SAT)} \ v \ I_C$



$h_{FE} \ v \ I_C$

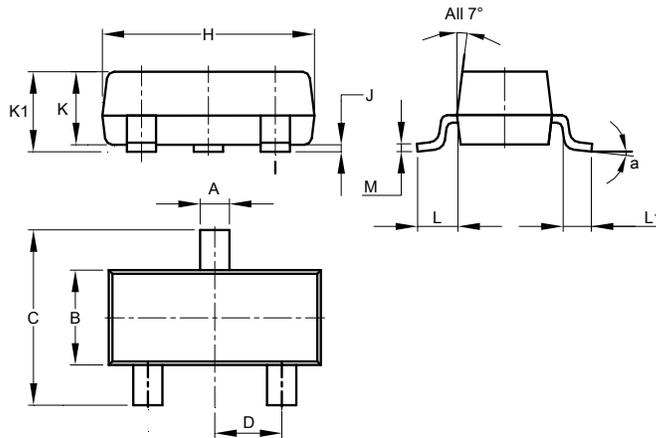


$V_{BE(SAT)} \ v \ I_C$



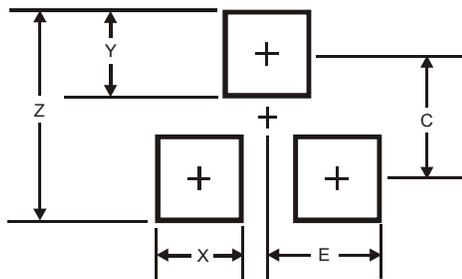
$V_{BE(ON)} \ v \ I_C$

Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.